polishing said substrate to remove a first portion of said selected amount of material by holding said substrate against a polishing pad with a polishing force while applying a polishing solution to said polishing pad;

rinsing said polishing pad with a rinsing fluid; and

polishing said substrate to remove a second portion of said selected amount of material by holding said substrate against said polishing pad with a polishing force while applying said polishing fluid to said polishing pad, wherein the polishing pad is not roughened by a pad conditioner between polishing the first and second portions of the material.

7. (Amended) A multistep method of polishing a semiconductor substrate in an inline polishing that includes at least first and second polishing stations, wherein said first polishing station includes a first polishing pad and said second polishing station includes a second polishing pad, said method comprising:

transferring said substrate to said first polishing station;

polishing said substrate to remove a first portion of material by holding said substrate against said first polishing pad with a polishing force while applying a first polishing solution to said first polishing pad;

rinsing said first polishing pad with a rinsing fluid;

polishing said substrate to remove a second portion of material by holding said substrate against said first polishing pad with a polishing force while applying said first polishing fluid to said first polishing pad, wherein the polishing pad is not roughened by a pad conditioner between polishing the first and second portions of the material;

transferring said substrate to said second polishing station; and

polishing said substrate to remove a third portion of material by holding said substrate against said second polishing pad with a polishing force while applying a second polishing solution to said second polishing pad.

REMARKS

Claims 1 and 7 have been amended and claims 2-6 and 8-13 remain unchanged. Thus, claims 1-13 are pending.

Claims 1 and 3 stand rejected under 35 U.S.C. 102(b) as being anticipated by Yoshida et al. (JP 11-138418).